Problem Set & Solution

1. ((Spoints)) (a) When a reversed biased source-to-substrate voltage is applied. the depletion region of source-substrate region junction midens, so more gate voltage should be applied to invert the Channel (5')

(b) Subthreshold conduction refers to the phenomenon where the drain current (ID) exists even when input voltage (s) less than or equal to the threshold voltage (VGS \le Vt) (3')

Plot: In

(c) Channel length modulation means when the MOSFET is biased in the Saturation region, the effective channel length is not a constant

but depends on drainto-source voltage. (31)

1-V curve: 10 | Saturation "-" Solid line: with channel length modulat:

Resistive "---" dashed line: without ~

= Vos (2')

2. (20 points) 5/+5/+5/+5'

(a) |Vas| = 0.20 |Vas - VT| = 0.40 |Since |Vas - VT|, in linear mode (2)

ID = kp \(\frac{W}{L} \) |Vas - VT| = 0.40 |Since |Vas| < |Vas - VT|, in linear mode (2)

ID = kp \(\frac{W}{L} \) |Vas - VT| = 0.40 |Since |Vas| > |Vas - VT| \(\text{in Scturation mode} \) (2)

ID = \frac{1}{2} kp \(\frac{W}{L} \) |Vas - VT| = 0.40 |Since |Vas| > |Vas - VT| \(\text{in Scturation mode} \) (2)

ID = \frac{1}{2} kp \(\frac{W}{L} \) |Vas - VT| = 0.80 |Since |Vas| > |Vas - VT| \(\text{in Scturation mode} \) (2)

ID = \frac{1}{2} kp \(\frac{W}{L} \) |Vas - VT| = 0.80 |Since |Vas| > |Vas - VT| \(\text{in Scturation mode} \) (2)

ID = \frac{1}{2} kp \(\frac{W}{L} \) |Vas - VT| = 0.80 |Since |Vas| > |Vas - VT| \(\text{in Scturation mode} \) (2)

ID = \frac{1}{2} kp \(\frac{W}{L} \) |Vas - VT| = 0.80 |Vas - VT| \(\text{in Sct mode} \) |Vas - VT| \(\text{in Scturation mode} \) (2)

ID = \frac{1}{2} kp \(\frac{W}{L} \) |Vas - VT| = 0.80 |Vas - VT| \(\text{in Sct mode} \) |Vas - VT| \(\text{in Sct mod

Rosistive; Saturation VGG=1,8V JUBS = 0,6V 3 VPS (V) (b) \$\overline{\text{lo(sat)}} = \overline{\text{WUnCox}}{2L} (VGS-V1). Slope= $\sqrt{\frac{11\times10^{-7}\times20}{2L}} = \sqrt{\frac{425\times\frac{3.9\times8.95\times10^{-14}}{11\times10^{-7}\times20}}{2\times1.2}} = 0.0333 (F/V.5)^{\frac{1}{2}}$ (1') Plot: Ilsism) When Vas= 2.4V. []orsat) = 2.0557(mA) 2.055/64) VT= 0,44 Vas (31) (c) When DEVOSE VI= 0.45VVID=0A und when VGs > VistVT linear region -10=11. (c) + 1/0. / slope = 425 x 3.9x 8.85x10-10 x 70=2,223x1035 Plot: IspmA) VT=0.45V 7.40 VGS (V). (51) 4. (5 points) Pfp= kt | nMa = 0.0259 × |n 1016 = 0.347 V (1) SVT= VT-VT= 1 [29fp+V93 - 124fp] 0.5-VT = 0.12x (J0.347x2+2.5 -J0.347x2) (2') => VT~ 0.386V ('Y) 5. 120 points) 5+5+545

(a) $\Phi_{fp} = \frac{1}{4} \ln \frac{Na}{ni} = 0.0259 \times \ln \frac{2 \times 10^{16}}{1.5 \times 10^{10}} \approx 0.365 \text{V}$ Vos (sat) = VGS - VT = 1 - 0.4 = 0.6 V (2')



Δ = [25s [JOFP + VDS - J OFFT VDS (Sat)] = [2X 11,7 x8.8t x 10-14 x J 0.365+2 - J 0.365+0.6] ~[1,413×10-5 am] (31) (b) Vosisat)=VGS-VT = 1-0.4=0.6V. (21)=2.544×10-5×(J0.365+4-J0.365+a6)= ~ 2.816× 10-5 am (31) (C) Vas (sat)=Vas-VT = 2-0.4= 1.6V. BL= 2.54U x10-5x (Jo.365+ Z-Jo.365+66)= 3.462x10-6cm (3' (d) Vosisatj= 1.6V(2) = 2.544×10-5x(Ja365+4-Ja365+1.6)~[1.749×10-5 cm [3]) 6. (lopoints) Since Voscsat) = VGS -VT. VGS= VoscSats+VT= 5V+1U=6V (1) When Vos=10V > Vos, (sat) in saturation made g= dlos = 0 (31) Igm (sat) = dlos = WunCox (Vas-VT) = kn (Vas-VT) Since Zoisat) = En (VGs-VT)2 => O.IMA= Exx(5V)2=> kn = 8x10-6 A/V2 gmisati= 8x10-6x5 = 4x10-55 (31) For Vos=IV. (1') For Vos=JV (1') For VDS = 10V. S D (1) 7. (15 points) 54548 (a) ID = Is evaslavt = e (Vas-Vas)/hvt Vas-Vas = nVtln ID for n=1. Vas'-Vas= 0.0259x | n 10= 0.0596V (b) for n=1.5, Vas-Vas= 1.5×0.0×9×1/10~ [0.0895V] (5') (afor n=21, VG3-V6s-21/x0.0259xlnlo=[0,125V[5])

